

74HC251; 74HCT251

8-input multiplexer; 3-state

Rev. 3 — 9 July 2013

Product data sheet

1. General description

The 74HC251; 74HCT251 is an 8-bit multiplexer with eight binary inputs (I0 to I7), three select inputs (S0 to S2) and an output enable input (\overline{OE}). The select inputs select one of the eight binary inputs and route it to the complementary outputs (Y and \overline{Y}). A HIGH on \overline{OE} causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

2. Features and benefits

- Input levels:
 - ◆ For 74HC251: CMOS level
 - ◆ For 74HCT251: TTL level
- Low-power dissipation
- Non-inverting data path
- Specified in compliance with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2 000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

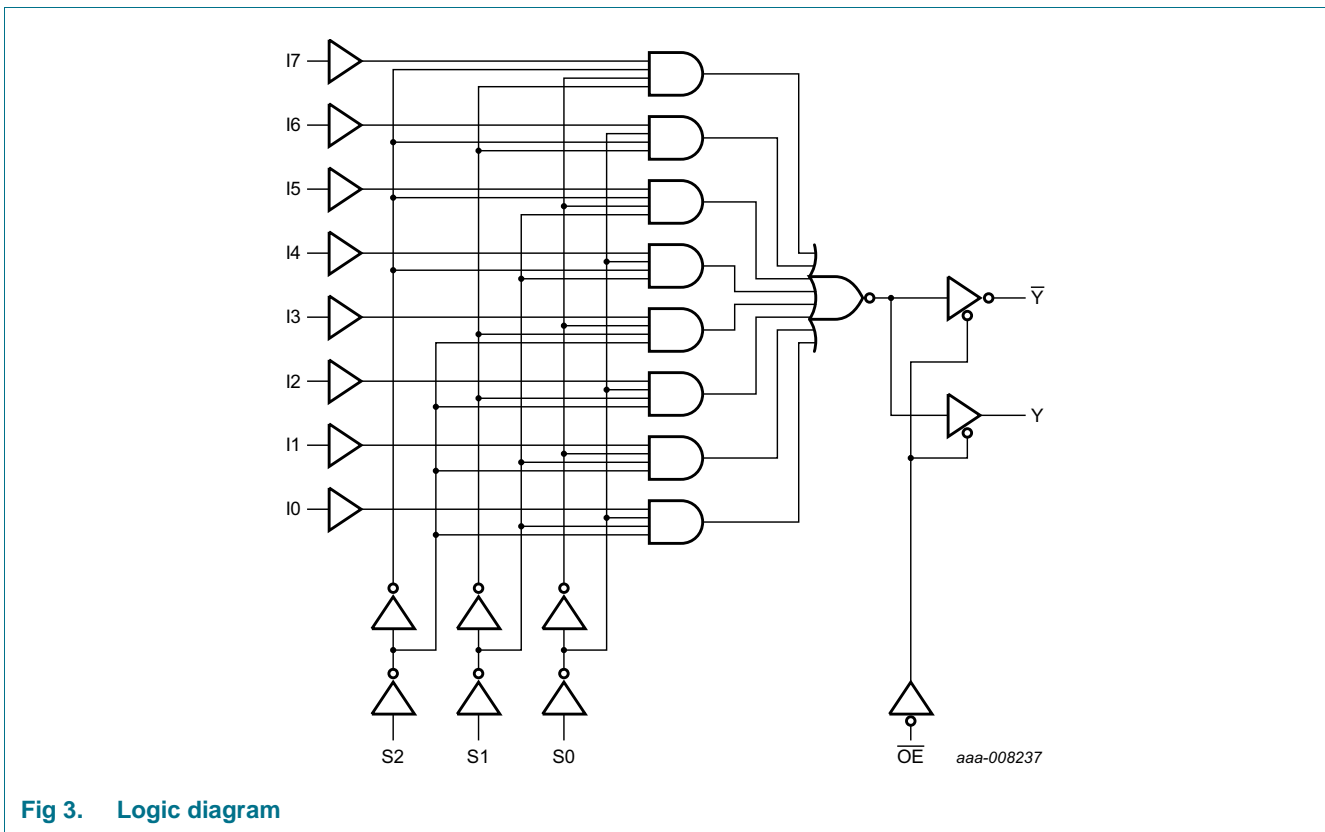
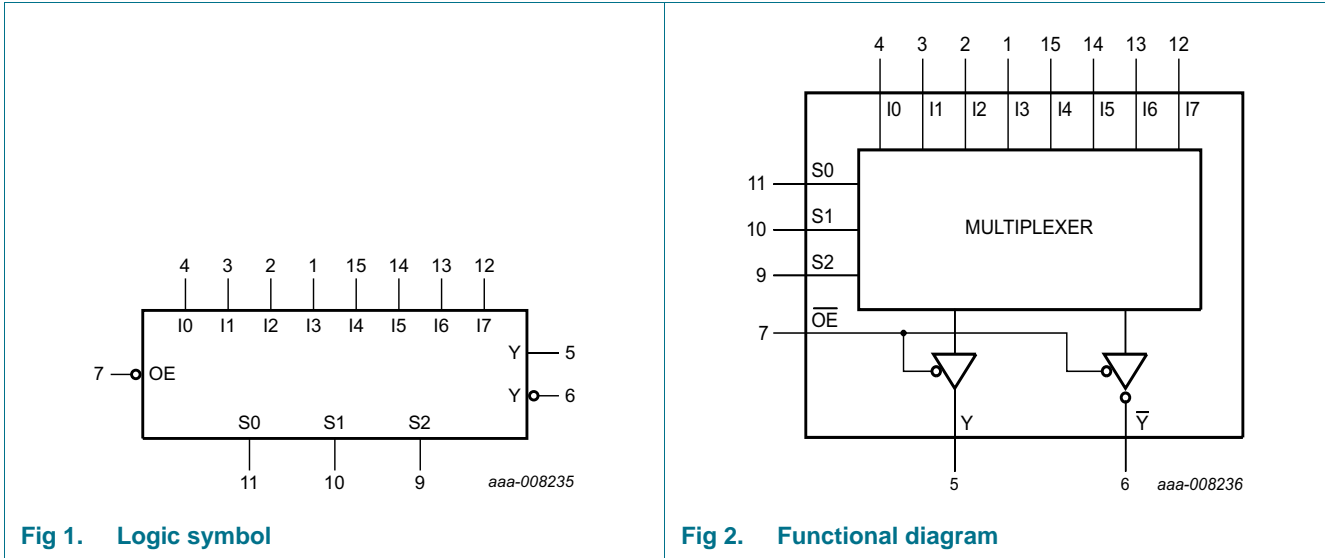
3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC251N	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT251N				
74HC251D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT251D				
74HC251DB	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT251DB				
74HC251PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT251PW				

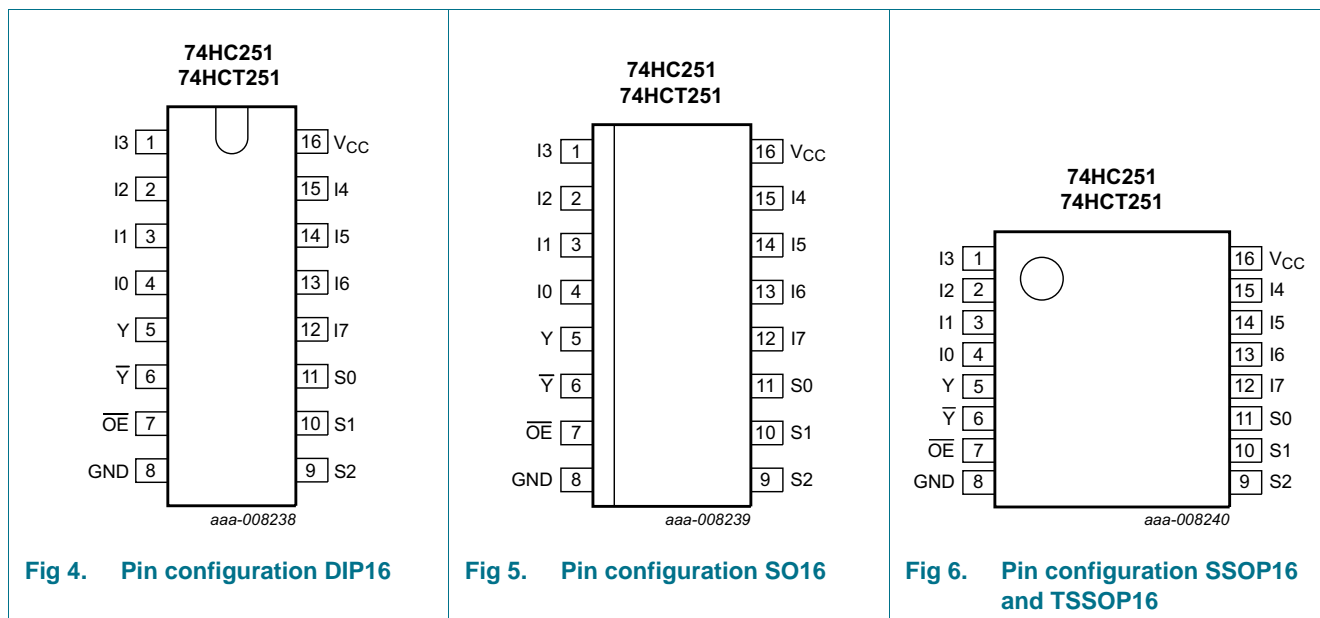


4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
I0 to I7	4, 3, 2, 1, 15, 14, 13, 12	data inputs
Y	5	multiplexer output
\bar{Y}	6	complementary multiplexer output
\overline{OE}	7	output enable input (active LOW)
GND	8	ground (0 V)
S0, S1, S2	11, 10, 9	common data select inputs
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Input												Output	
OE	S2	S1	S0	I0	I1	I2	I3	I4	I5	I6	I7	Y	Y
H	X	X	X	X	X	X	X	X	X	X	X	Z	Z
L	L	L	L	L	X	X	X	X	X	X	X	H	L
L	L	L	L	H	X	X	X	X	X	X	X	L	H
L	L	L	H	X	L	X	X	X	X	X	X	H	L
L	L	L	H	X	H	X	X	X	X	X	X	L	H
L	L	H	L	X	X	L	X	X	X	X	X	H	L
L	L	H	L	X	X	H	X	X	X	X	X	L	H
L	L	H	H	X	X	X	L	X	X	X	X	H	L
L	L	H	H	X	X	X	H	X	X	X	X	L	H
L	H	L	L	X	X	X	X	L	X	X	X	H	L
L	H	L	L	X	X	X	X	H	X	X	X	L	H
L	H	L	H	X	X	X	X	X	L	X	X	H	L
L	H	L	H	X	X	X	X	X	H	X	X	L	H
L	H	H	L	X	X	X	X	X	X	L	X	H	L
L	H	H	L	X	X	X	X	X	X	H	X	L	H
L	H	H	H	X	X	X	X	X	X	X	L	H	L
L	H	H	H	X	X	X	X	X	X	X	H	L	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	-	±20	mA
I _O	output current	V _O = -0.5 V to (V _{CC} + 0.5 V)	-	±25	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C			
	DIP16 package		[1] -	750	mW
	SO16 package		[2] -	500	mW
	(T)SSOP16 package		[3] -	500	mW

[1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

[2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] For SSOP16 and TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC251			74HCT251			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +85 °C		T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC251										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
		V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.5	-	±5.0	-	±10.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
C _I	input capacitance		-	3.5	-					pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +85 °C		T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT251										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _{CC} = 5.5 V; V _O = V _{CC} or GND per input pin; other inputs at V _{CC} or GND; I _O = 0 A	-	-	±0.5	-	±5.0	-	±10	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	-	80	-	160	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A								
		per input pin; I _n inputs	-	100	360	-	450	-	490	μA
		per input pin; $\overline{\text{OE}}$ input	-	150	540	-	675	-	735	μA
		per input pin; S _n input	-	150	540	-	675	-	735	μA
C _I	input capacitance		-	3.5	-					pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 10](#).

Symbol	Parameter	Conditions	$T_{amb} = 25\text{ °C}$			$T_{amb} = -40\text{ °C}$ to $+85\text{ °C}$		$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC251										
t_{pd}	propagation delay	In to Y; see Figure 7 [1]								
		$V_{CC} = 2.0\text{ V}$	-	50	170	-	215	-	255	ns
		$V_{CC} = 4.5\text{ V}$	-	18	34	-	43	-	51	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	15	-	-	-	-	-	ns
		$V_{CC} = 6.0\text{ V}$	-	14	29	-	37	-	43	ns
		In to \bar{Y} ; see Figure 7 [1]								
		$V_{CC} = 2.0\text{ V}$	-	55	175	-	220	-	265	ns
		$V_{CC} = 4.5\text{ V}$	-	20	35	-	44	-	53	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	17	-	-	-	-	-	ns
		$V_{CC} = 6.0\text{ V}$	-	16	30	-	37	-	45	ns
		Sn to Y; see Figure 8 [1]								
		$V_{CC} = 2.0\text{ V}$	-	66	205	-	255	-	310	ns
		$V_{CC} = 4.5\text{ V}$	-	24	41	-	51	-	62	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	20	-	-	-	-	-	ns
		$V_{CC} = 6.0\text{ V}$	-	19	35	-	43	-	53	ns
		Sn to \bar{Y} ; see Figure 8 [1]								
$V_{CC} = 2.0\text{ V}$	-	69	205	-	255	-	310	ns		
$V_{CC} = 4.5\text{ V}$	-	25	41	-	51	-	62	ns		
$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	21	-	-	-	-	-	ns		
$V_{CC} = 6.0\text{ V}$	-	20	35	-	43	-	53	ns		
t_{en}	enable time	\overline{OE} to Y, \bar{Y} ; see Figure 8 [2]								
		$V_{CC} = 2.0\text{ V}$	-	36	140	-	175	-	210	ns
		$V_{CC} = 4.5\text{ V}$	-	13	28	-	35	-	42	ns
t_{dis}	disable time	\overline{OE} to Y, \bar{Y} ; see Figure 8 [3]								
		$V_{CC} = 2.0\text{ V}$	-	39	140	-	170	-	210	ns
		$V_{CC} = 4.5\text{ V}$	-	14	28	-	35	-	42	ns
t_t	transition time	Y, \bar{Y} ; see Figure 7 [4]								
		$V_{CC} = 2.0\text{ V}$	-	19	75	-	95	-	110	ns
		$V_{CC} = 4.5\text{ V}$	-	7	15	-	19	-	22	ns
C_{PD}	power dissipation capacitance	$V_{CC} = 6.0\text{ V}$	-	6	13	-	16	-	19	ns
		$C_L = 50\text{ pF}; f = 1\text{ MHz}; V_1 = \text{GND to } V_{CC}$ [5]	-	44	-	-	-	-	-	pF

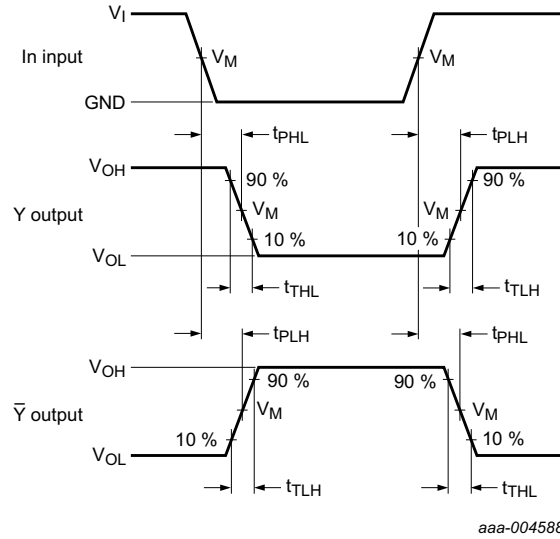
Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 10](#).

Symbol	Parameter	Conditions	$T_{amb} = 25\text{ °C}$			$T_{amb} = -40\text{ °C}$ to $+85\text{ °C}$		$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT251										
t_{pd}	propagation delay	In to Y; see Figure 7 [1]								
		$V_{CC} = 4.5\text{ V}$	-	22	35	-	44	-	53	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	19	-	-	-	-	-	ns
		In to \bar{Y} ; see Figure 7 [1]								
		$V_{CC} = 4.5\text{ V}$	-	22	35	-	44	-	53	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	19	-	-	-	-	-	ns
		Sn to Y; see Figure 8 [1]								
		$V_{CC} = 4.5\text{ V}$	-	24	44	-	55	-	66	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	20	-	-	-	-	-	ns
t_{en}	enable time	Sn to \bar{Y} ; see Figure 8 [1]								
		$V_{CC} = 4.5\text{ V}$	-	25	44	-	55	-	66	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	21	-	-	-	-	-	ns
t_{dis}	disable time	\bar{OE} to Y, \bar{Y} ; see Figure 8 [2]								
		$V_{CC} = 4.5\text{ V}$	-	13	28	-	35	-	42	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	13	-	-	-	-	-	ns
t_{dt}	disable time	\bar{OE} to Y, \bar{Y} ; see Figure 8 [3]								
		$V_{CC} = 4.5\text{ V}$	-	14	28	-	35	-	42	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	18	-	-	-	-	-	ns
t_t	transition time	Y, \bar{Y} ; see Figure 7 [4]								
		$V_{CC} = 4.5\text{ V}$	-	7	15	-	19	-	22	ns
C_{PD}	power dissipation capacitance	$C_L = 50\text{ pF}; f = 1\text{ MHz}; V_i = \text{GND to } V_{CC}$ [5]	-	46	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [2] t_{en} is the same as t_{PZH} and t_{PZL} .
- [3] t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- [4] t_t is the same as t_{THL} and t_{TLH} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

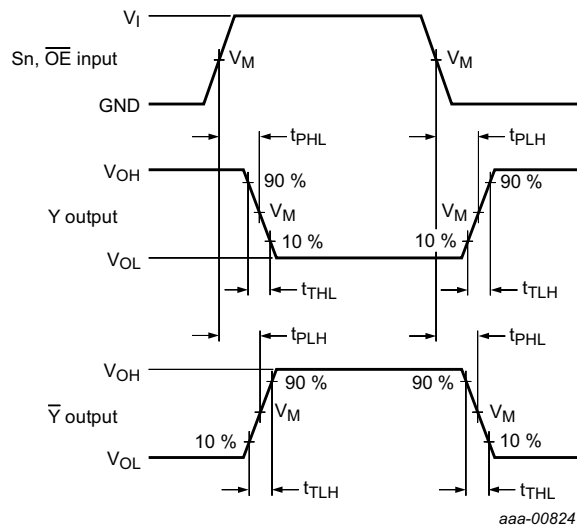
11. Waveforms



Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

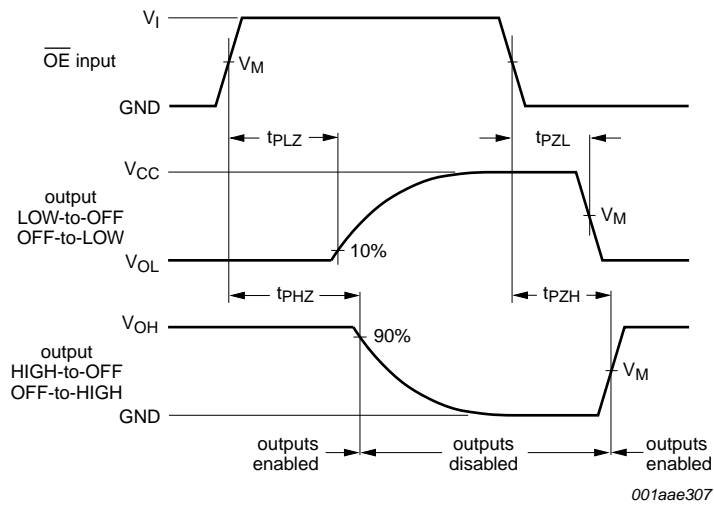
Fig 7. Propagation delay input (In) to output (Y, \bar{Y}) and the output (Y, \bar{Y}) transition time



Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 8. Propagation delay input (S_n , \overline{OE}) to output (Y, \bar{Y})



Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 9. Enable and disable times

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC251	$0.5V_{CC}$	$0.5V_{CC}$
74HCT251	1.3 V	1.3 V

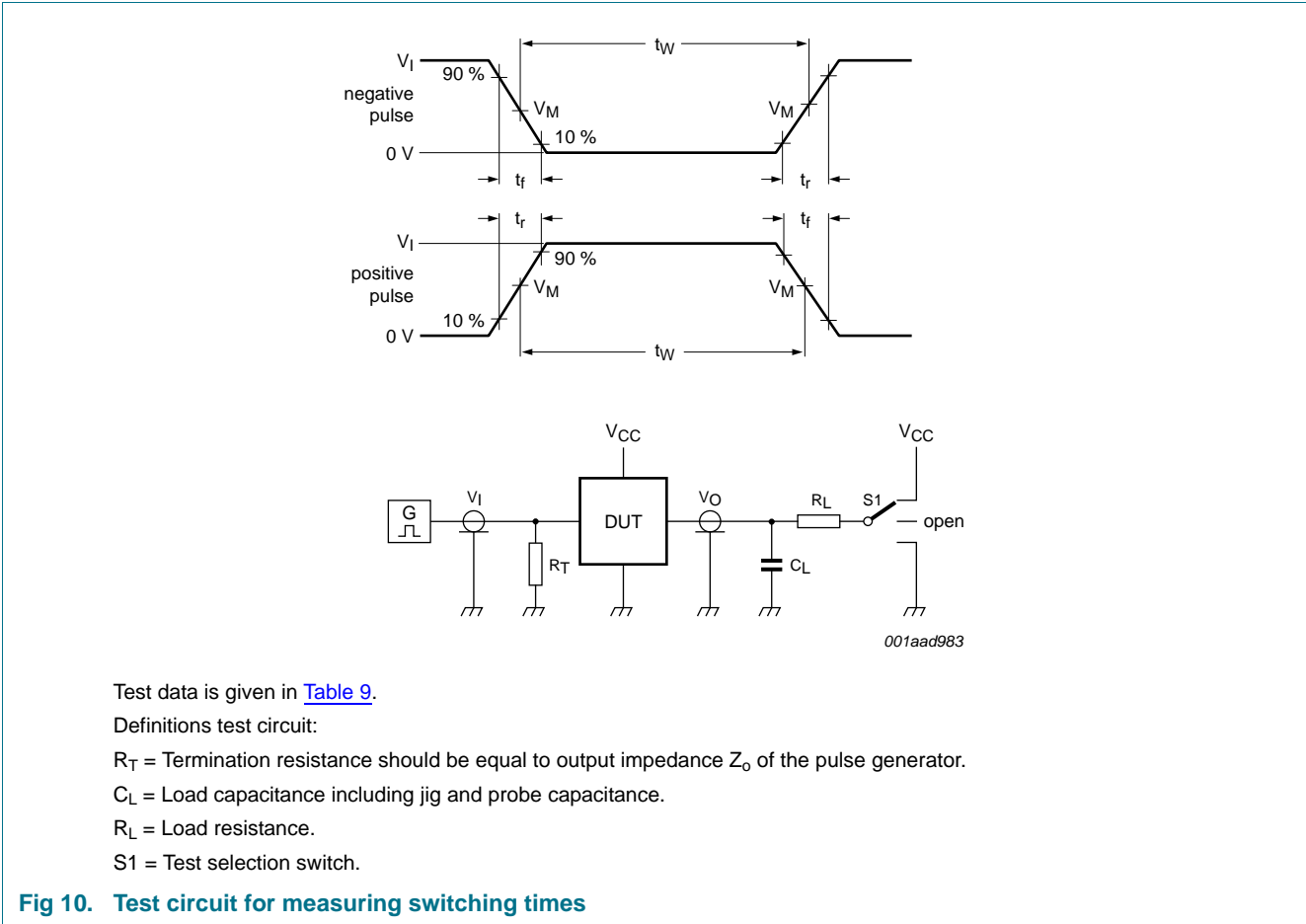


Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC251	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT251	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4

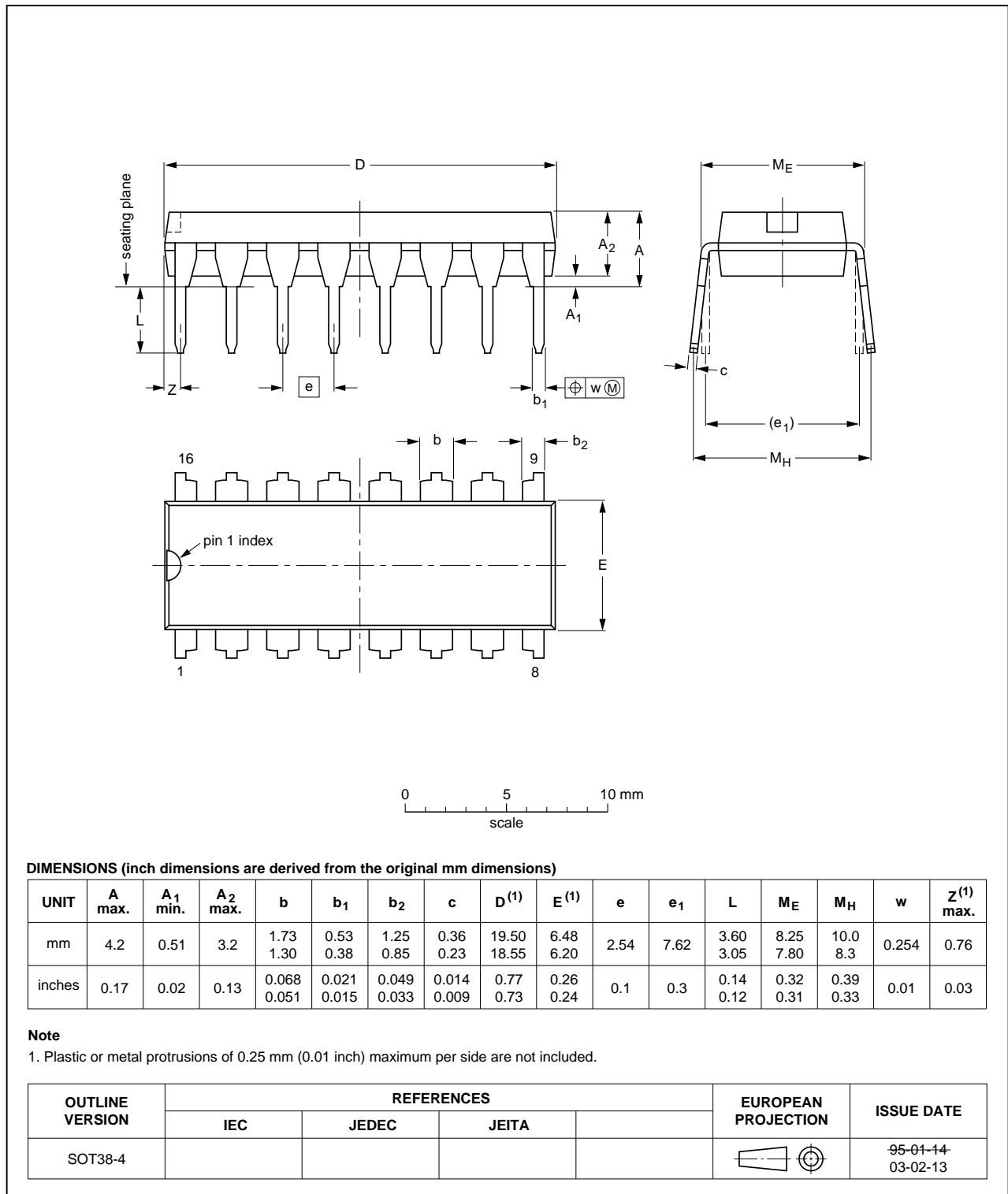


Fig 11. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

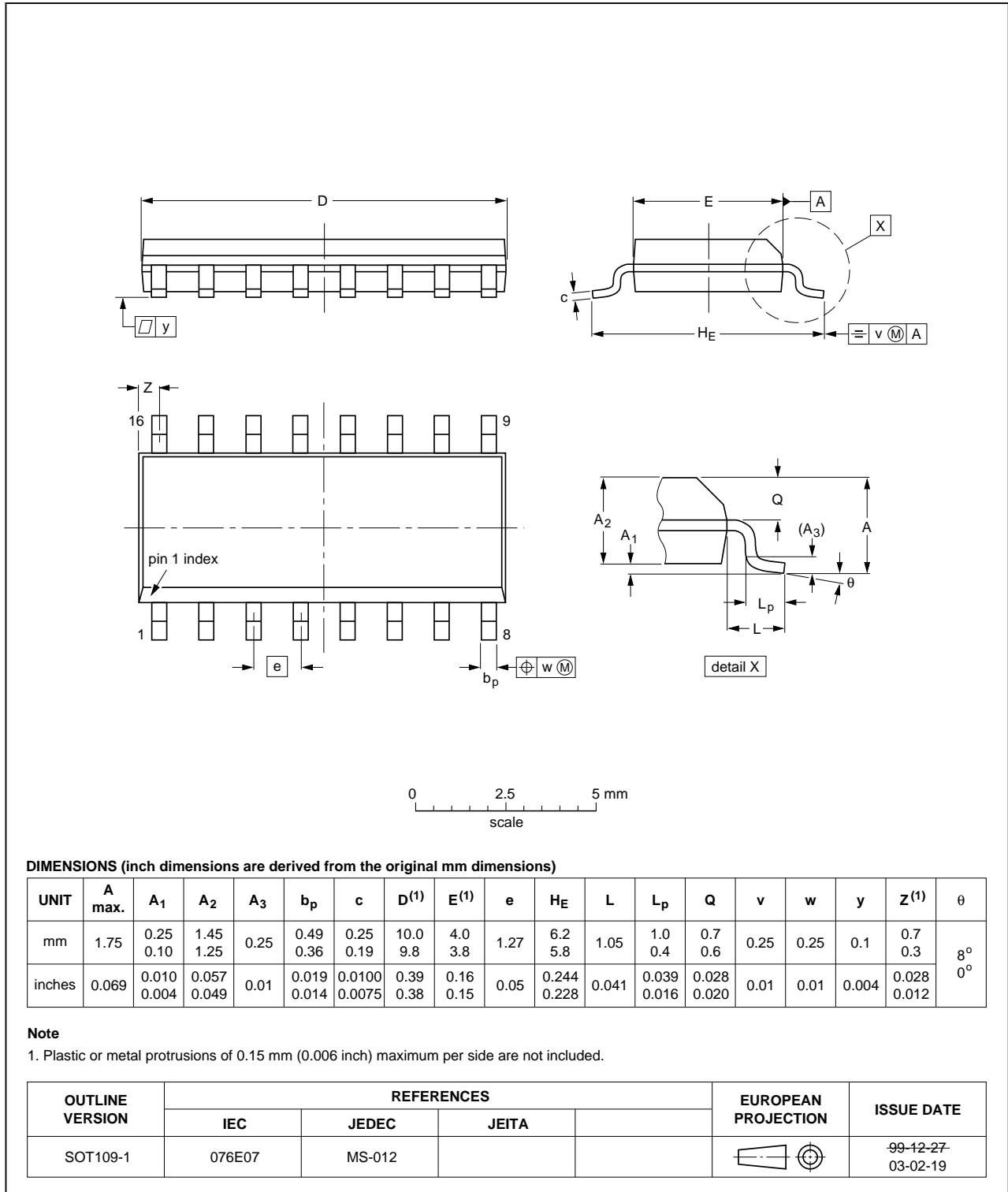


Fig 12. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

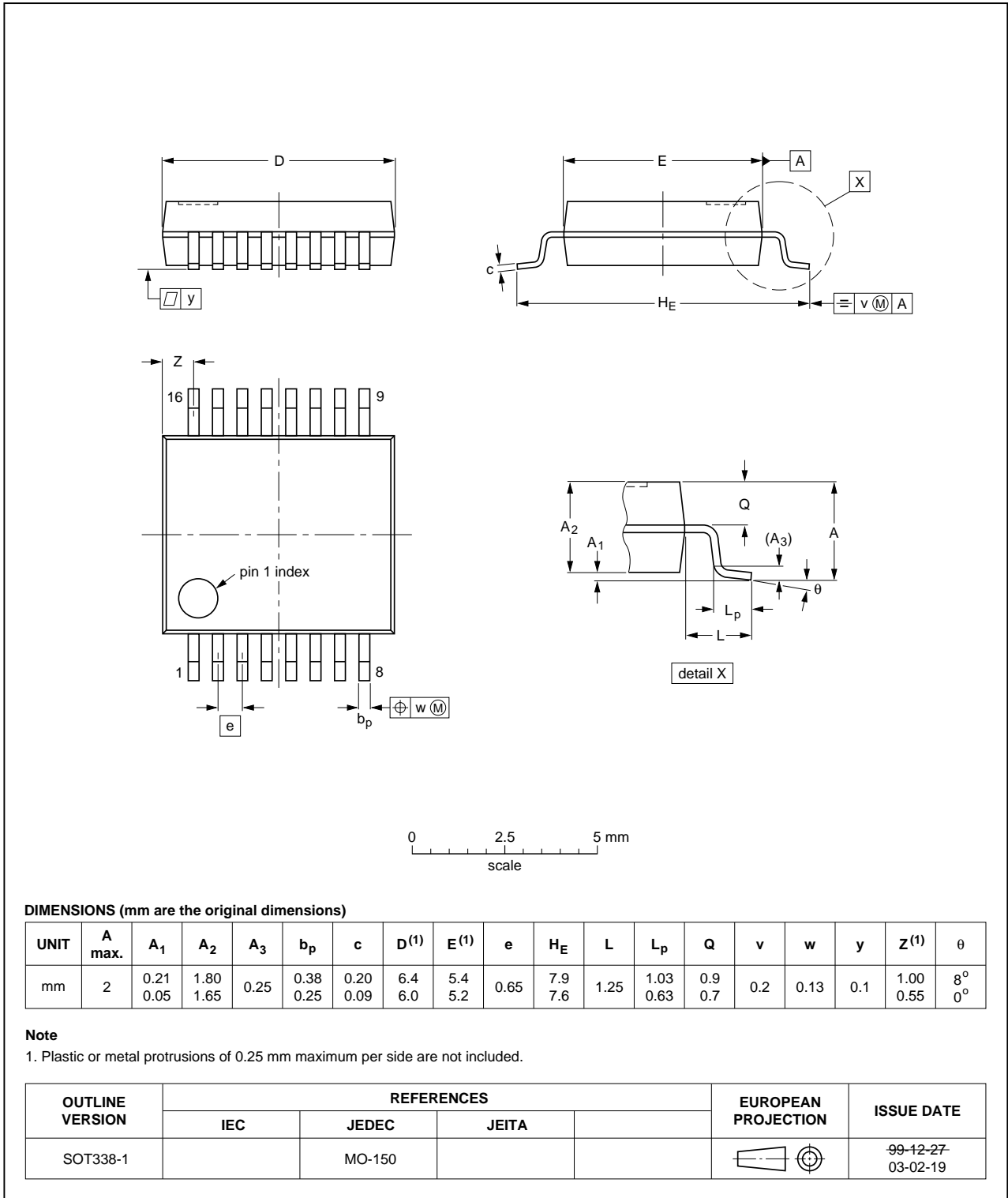


Fig 13. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

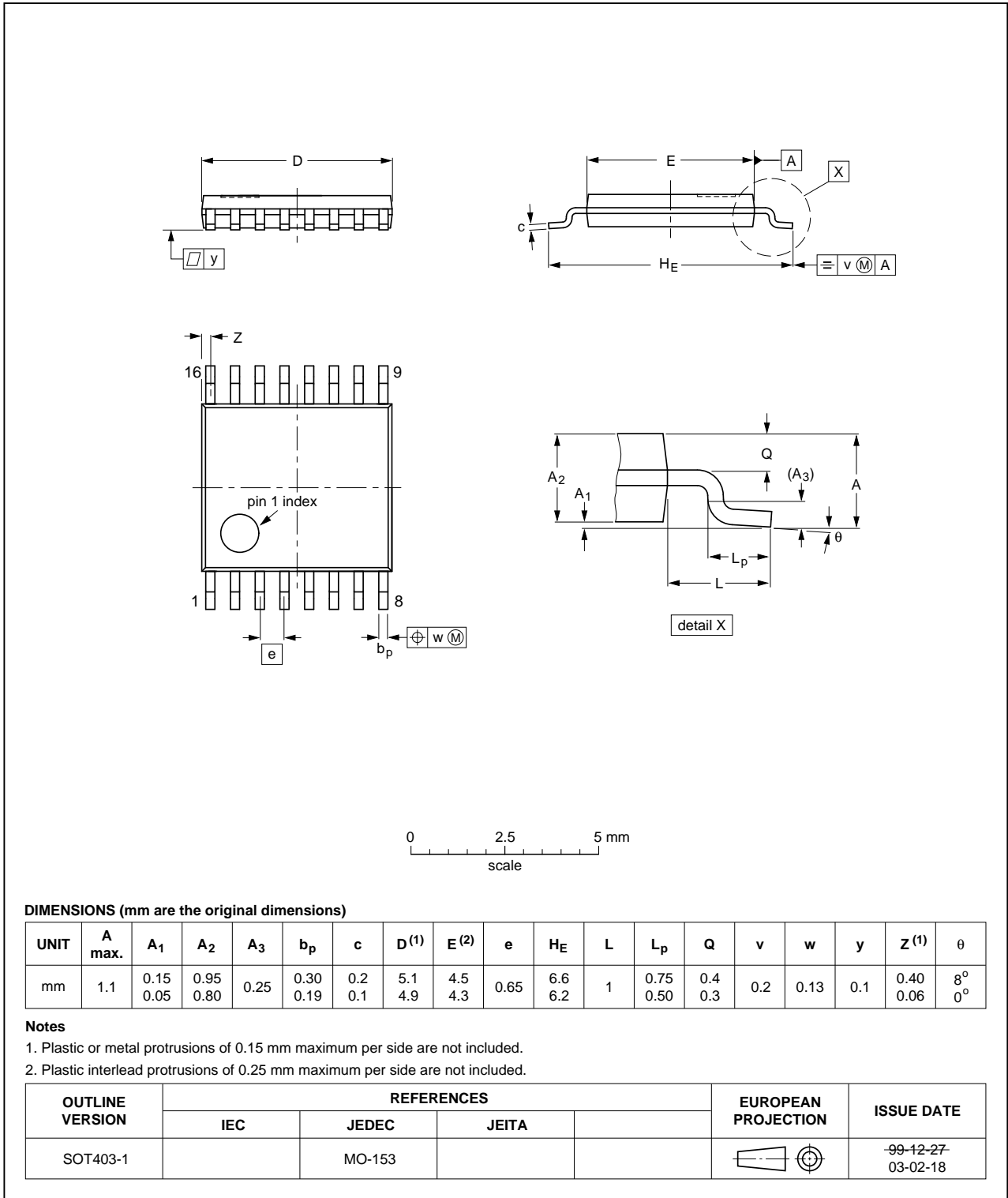


Fig 14. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT251 v.3	20130709	Product data sheet	-	74HC_HCT251_CNV v.2
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. 			
74HC_HCT251_CNV v.2	19970828	Product specification	-	

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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